SERTECH LABS
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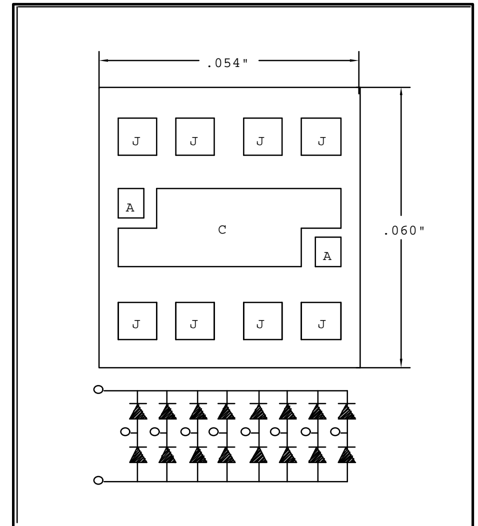
16M0

DIE SPECIFICATION

60V 300mA
MONOLITHIC DIODE ARRAY

FEATURES:

- 16 DIODE CORE DRIVER
- trr < 20 ns
- RUGGED AIR-ISOLATED CONSTRUCTION
- LOW REVERSE LEAKAGE CURRENT



Absolute Maximum Ratings:

Symbol		Parameter	Limit	Unit
VBR(R)	*1 *2	Reverse Breakdown Voltage	60	Vdc
IO	*1	Continuous Forward Current	300	mAdc
IFSM	*1	Peak Surge Current (tp= 1/120 s)	500	mAdc
Top		Operating Junction Temperature Range	-65 to +150	°C
Tstg		Storage Temperature Range	-65 to +200	°C

NOTE 1: Each Diode
NOTE 2: Pulsed: PW = 100ms max.; duty cycle ≤ 20%

Electrical Characteristics (Per Diode) @ 25°C unless otherwise specified

Symbol	Parameter	Conditions	Min	Max	Unit
BV1	Breakdown Voltage	IR = 10uAdc	60		
Vf1	Forward Voltage	IF = 100mAdc *1		1	Vdc
Vf2	Forward Voltage	IF = 500mAdc *1		1.5	Vdc
IR1	Reverse Current	VR = 40 Vdc		0.1	uAdc
Ct	Capacitance (pin to pin)	VR = 0 Vdc; f = 1 MHz		8.0	pF
tfr	Forward Recovery Time	IF = 500mAdc		40	ns
trr	Reverse Recovery Time	IF = IR = 200mAdc, irr = 20 mAdc, RL = 100 ohms		20	ns

NOTE 1: Pulsed: PW = 300us +/- 50us, duty cycle ≤ 2%, 90us after leading edge

Packaging Options:
W: Wafer (100% probed) U: Wafer (sample probed)
D: Chip (Waffle Pack) B: Chip (Vial)
V: Chip (Waffle Pack, 100% visually inspected) X: Other

Processing Options:
Standard: Capable of JANTXV application (No Suffix)
Suffix C: Commercial
Suffix S: Capable of S-Level equivalent applications

Metallization Options:

Standard: Al Top / Au Backside (No Dash #)

ORDERING INFORMATION
PART #: 16M0_ _- _
First Suffix Letter: Packaging Option
Second Suffix Letter: Processing Option
Dash #: Metallization Option

Sertech reserves the right to make changes to any product design, specification or other information at any time without prior notice.

MSC1024.PDF Rev - 12/3/98